

## REMARKS

## 1. EXAMINER'S AMENDMENT

An examiner's amendment to the record appears below.

5 Should the changes and/or be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee.

10 The application has been amended as follows, to correct minor grammatical informalities identified in the specification.

In claim 1, line 2, change "substrate, forming" to -substrate and forming--.

15 In claim 2 (line 2) and claim 22 (line 2) change "the testing area" to -a testing area--.

In claim 6 (line 1) and claim 31 (line 1), change "Fowler-Nordehim" to -Fowler Nordheim--.

20 In claim 9 and claim 33 (line 2), change "voltage, the" to --voltage and the --.

In claim 10 and claim 34 (line 2), change "voltage, the" to --voltage and the --.

25 In claim 11 and claim 15 and claim 19 and claim 24 and claim 28 and claim 35 and claim 39 and claim 43 (line 1), change "comprises" to -comprising--.

In the abstract, line 1, change "a wafer" to -wafer--.

At [0002], line 2, change "particularly, to a method" to -particularly, relates to a method--.

30 At [0032] (lines 2 and 4), [0034] (line 6), [0045] (line 1), change each occurrence of "Fowler-Nordehim" to -Fowler-Nordheim--.

At [0033], line 7, change "here, an tunnel" to -here, a tunnel--.

**Response:**

5 The Applicant agrees the examiner's amendment. The specification, claims, and abstract are amended as shown in the "AMENDMENTS TO THE SPECIFICATION" and the "AMENDMENTS TO THE CLAIMS", according to the examiner's suggestion. In paragraph [0002], the term  
10 "particularly, to a method" is changed to "particularly, relates to a method" due to an editorial error. In paragraphs [0032], [0034], and [0045], the terms "Fowler-Nordehim" are changed to "Fowler-Nordheim" due to typographic errors. In  
15 paragraph [0033], the term "here, an tunnel" is changed to "here, a tunnel" due to a typographic error. No new matter is introduced. Reconsideration of the corrected specification is hereby requested.

20 In claim 1, the term "substrate, forming" is changed to "substrate and forming" due to an editorial error. In claims 2 and 22, the terms "the testing area" are changed to "a testing area" due to editorial errors. In claims 6 and 31, the terms "Fowler-Nordehim" are  
25 changed to "Fowler-Nordheim" due to typographic errors. In claims 9, 33, 10, and 34, the terms "voltage, the" are changed to "voltage and the" due to editorial errors. In claims 11, 15, 19, 24, 28, 35, 39, and 43, the terms "comprises" are changed to "comprising" due  
30 to typographic errors. No new matter is introduced. Reconsideration of the corrected claims is hereby requested.

In line 1 of the abstract, the term "a wafer" is changed to "wafer" due to an editorial error. No new matter is introduced. Reconsideration of the corrected abstract is hereby requested.

## 2. Drawings

Applicant's drawings, particularly Fig.8, are seemingly informal. Applicant should formalize the drawings for better quality printing, in response to this action.

### Response:

Applicant's drawings in attorney's office look all right. In order to fulfill examiner's requirement, the attached sheets of drawings including Fig.1 to Fig.8 are resubmitted. Drawings in these sheets are formalized and have better printing quality.

## 3. Request for Continued Examination

### Response:

The Applicant has amended the following claims:

In claims 14 and 38, the terms "voltage, the" are also changed to "voltage and the" due to editorial errors. No new matter is introduced. In claim 25, the term "the memory cell is a flash memory cell" is deleted and the term "the flash memory cell" is changed to "a flash memory cell" due to a same editorial error. The sentence "and the oxide layer is a tunnel oxide layer of the flash memory cell" is added due to an editorial

error. The newly added portion is disclosed in paragraph [0033]. No new matter is introduced. In claim 26, the terms "the flash memory cell" are changed to "a non-volatile memory cell" or "the non-volatile  
5 memory cell" due to a same editorial error. The newly added portion is disclosed in paragraph [0004], [0005] and is regarded as common knowledge that those of ordinary skill in the art should know.

10 In claim 29, the term "tunnel oxide layer" is changed to "oxide layer" due to an editorial error. In claim 43, the terms "tunnel oxide layer" are changed to "oxide layer" and the term "in the memory cell" is deleted due to a same editorial error. In claim 32,  
15 the number "21" is changed to "28" due to an editorial error. No new matter is introduced. Reconsideration of the corrected claims is hereby requested.

Since the original claims 21-43 are too narrow, some  
20 of the terms in claims 21-43 are replaced with more general terms to broaden the original claims 21-43. The terms "semiconductor substrate" in claims 21-43 are changed to "substrate". The terms "first gate" are changed to "first conductive layer". The terms "first  
25 gate voltage" are changed to "first voltage". The terms "first gate leakage current" are changed to "first leakage current". The terms "second gate voltage" are changed to "second voltage". The terms "second gate leakage current" are changed to "second leakage  
30 current". The terms "second gate" are changed to "second conductive layer". The term "each gate voltage" is changed to "each voltage". The terms "third

gate voltage" are changed to "third voltage". The terms  
"third gate leakage current" are changed to "third  
leakage current". The terms " $-V_g$  curve" are changed  
to " $-V$  curve". The term "each gate leakage current"  
5 is changed to "each leakage current". Since all of the  
amendments are regarded as common knowledge that those  
of ordinary skill in the art should know, no new matter  
is introduced. Reconsideration of the amended claims  
is hereby requested.

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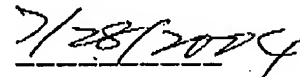
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Sincerely yours,

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communication and I will return your call promptly.)

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